Nitride semiconductors are expected to be the next generation power device. Mass production at low cost calls for a high quality nitride epitaxial wafer on large caliber Si substrate. NTT-AT produces an epitaxial wafer on 6 inch Si substrate with high quality you can trust.

Sheet resistivity distribution:
- Variation 6%
- Ave.: 440 ohm/sq.
- Mobility: 2180 cm²/Vs

Curvature radius of larger than 160m
- BOW: 34 µm
- SORI: 34 µm

Surface roughness: RMS ~0.25 nm (1µm field)

Surface defect density: ~2e9 cm⁻²

※The contents of this catalogue may be changed without previous notification. Also, measured values are not guaranteed value.

For more information:

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